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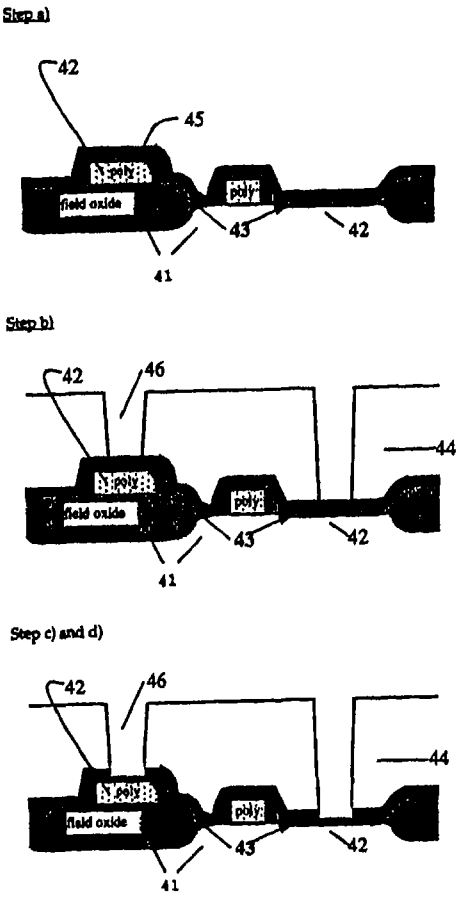


G00001

(54) Title: METHOD FOR REMOVAL OF SIC

(57) Abstract

The present invention is related to a method for removal of silicon carbide layers and in particular amorphous SiC of a substrate comprising the steps of: converting at least partly said exposed part of said carbide-silicon layer into an oxide-silicon layer by exposing said carbide-silicon layer to an oxygen containing plasma; and removing said oxide-silicon layer from said substrate. The present invention is also related to an integrated circuit implementing said method.





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